

RF Power LDMOS Transistor

N-Channel Enhancement-Mode Lateral MOSFET

RF power transistor suitable for industrial heating applications operating at 2450 MHz. Device is capable of both CW and pulse operation.

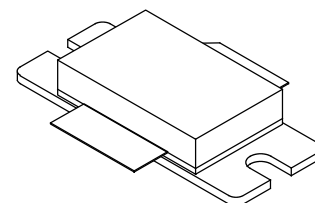
- Typical CW Performance at 2450 MHz, $V_{DD} = 28$ Vdc, $I_{DQ} = 1200$ mA, $P_{out} = 140$ W
Power Gain — 13.2 dB
Drain Efficiency — 45%
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2390 MHz, 140 W CW Output Power

Features

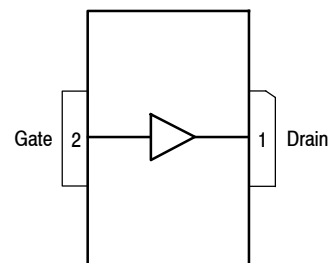
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- In Tape and Reel. R5 Suffix = 50 Units per 56 mm Tape Width, 13-inch Reel.

MHT1000HR5

**2450 MHz, 140 W CW, 28 V
INDUSTRIAL HEATING, RUGGED
RF POWER LDMOS TRANSISTOR**



NI-880H-2L



(Top View)

Note: The backside of the package is the source terminal for the transistor.

Figure 1. Pin Connections

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 82°C, 140 W CW	$R_{\theta JC}$	0.29	°C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C
Machine Model (per EIA/JESD22-A115)	A
Charge Device Model (per JESD22-C101)	III

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	500	nAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 1300\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	$V_{DS(on)}$	0.1	0.21	0.3	Vdc

Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2	—	pF
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Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1300\text{ mA}$, $P_{out} = 28\text{ W Avg.}$, $f = 2390\text{ MHz}$, 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset. IM3 measured in 3.84 MHz Bandwidth @ $\pm 10\text{ MHz}$ Offset. Input Signal PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	13	15.2	17	dB
Drain Efficiency	η_D	23	25	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-40	-38	dBc
Input Return Loss	IRL	—	-15	—	dB

1. Part internally matched both on input and output.

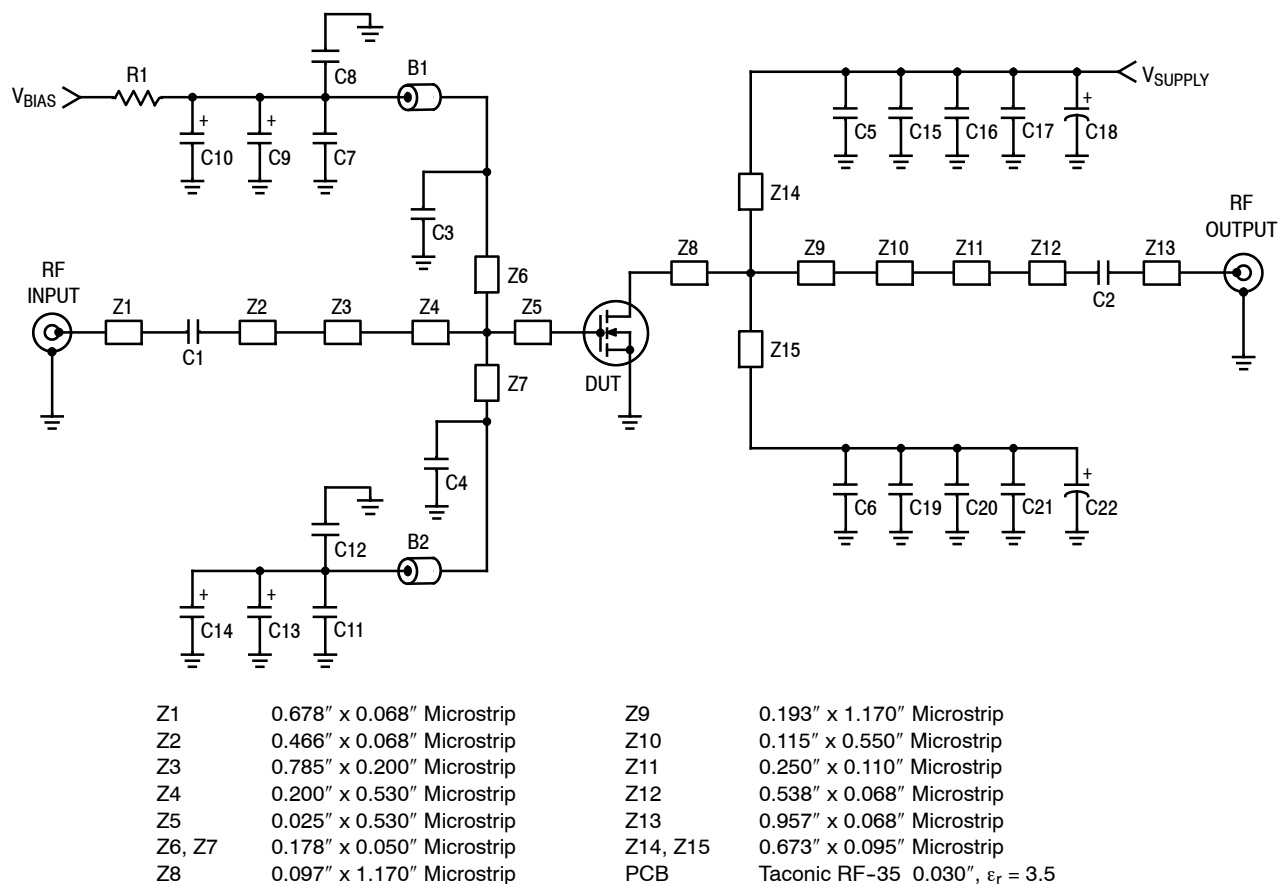
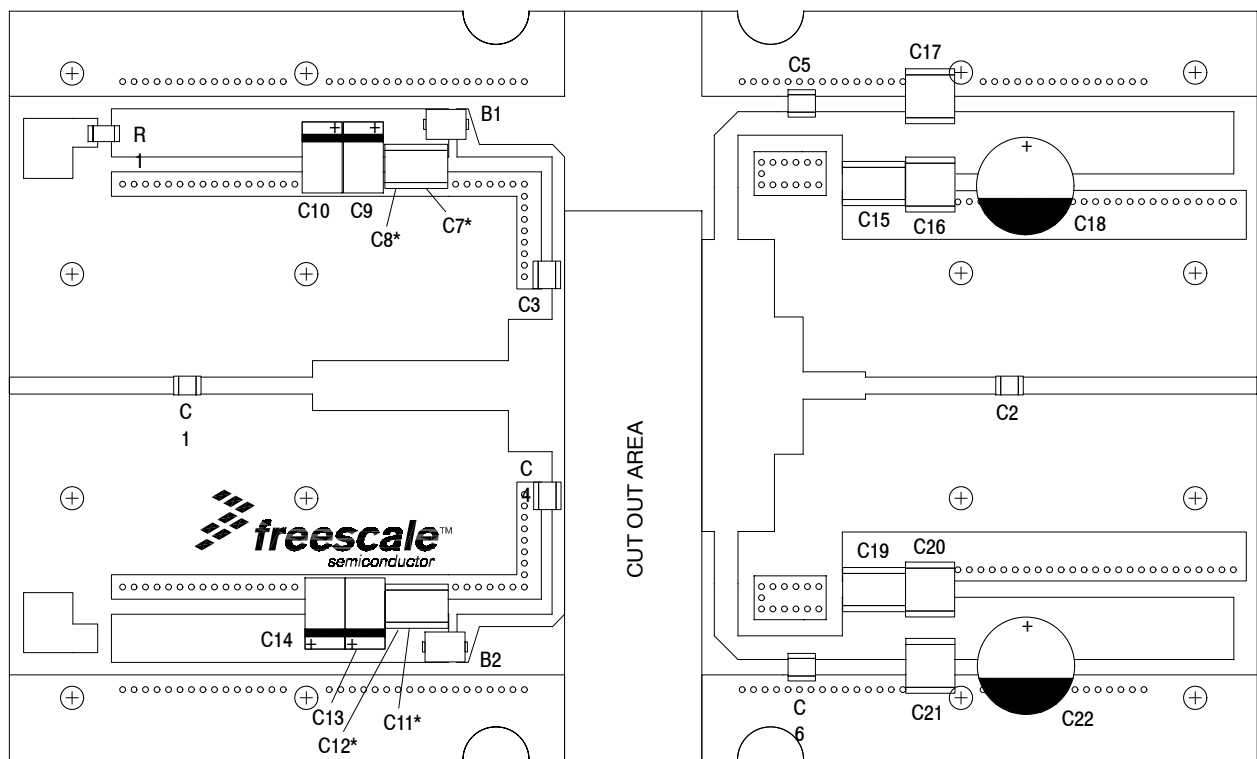


Figure 1. MHT1000HR5 Test Circuit Schematic — 2450 MHz

Table 5. MHT1000HR5 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B2	47 Ω , 100 MHz Short Ferrite Beads, Surface Mount	2743019447	Fair-Rite
C1, C2, C3, C4, C5, C6	5.6 pF Chip Capacitors	ATC600B5R6BT500XT	ATC
C7, C11	0.01 μ F, 100 V Chip Capacitors	C1825C103J1RAC	Kemet
C8, C12, C15, C19	2.2 μ F, 50 V Chip Capacitors	C1825C225J5RAC	Kemet
C9, C13	22 μ F, 25 V Tantalum Capacitors	T491D226M025AT	Kemet
C10, C14	47 μ F, 16 V Tantalum Capacitors	T491D476K016AT	Kemet
C16, C17, C20, C21	10 μ F, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata
C18, C22	220 μ F, 50 V Electrolytic Capacitors	2222-150-95102	Vishay
R1	240 Ω , 1/4 W Chip Resistor	CRC12062400FKEA	Vishay



* Stacked

Figure 2. MHT1000HR5 Test Circuit Component Layout

TYPICAL CHARACTERISTICS — 2450 MHz

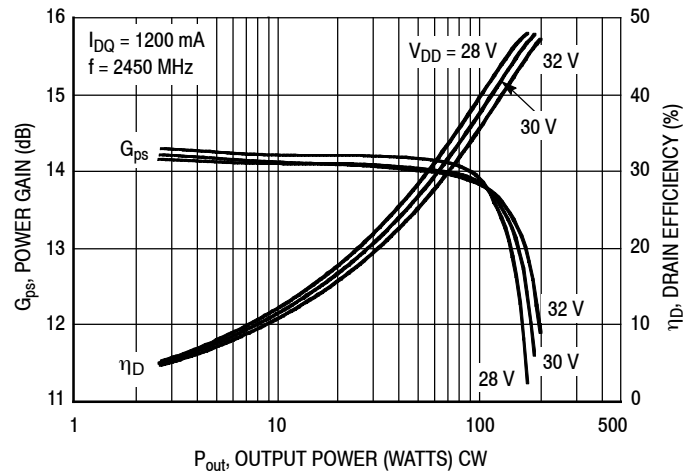


Figure 3. Power Gain and Drain Efficiency versus CW Output Power as a Function of V_{DD}

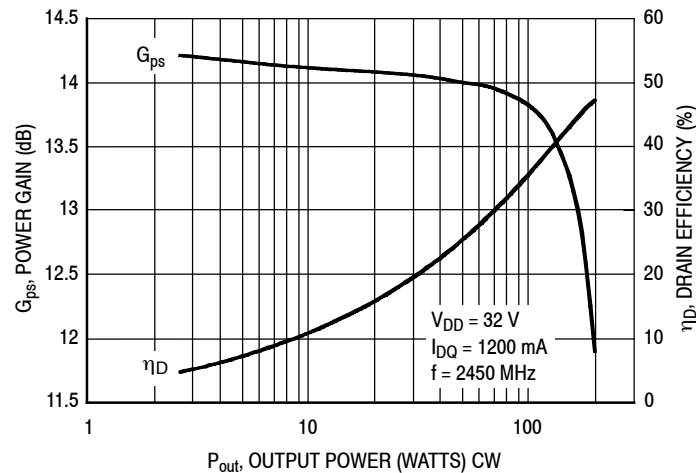


Figure 4. Power Gain and Drain Efficiency versus CW Output Power

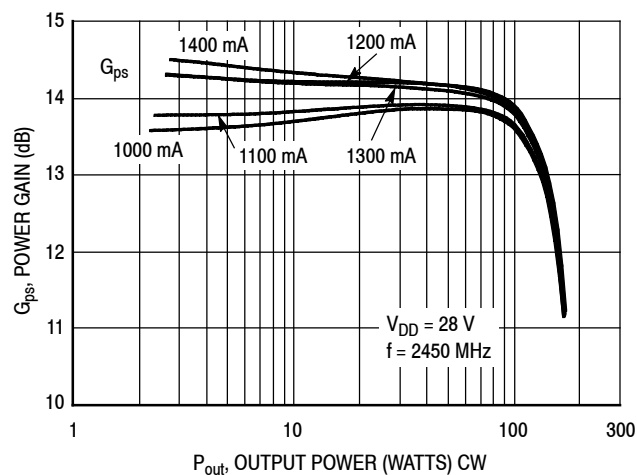
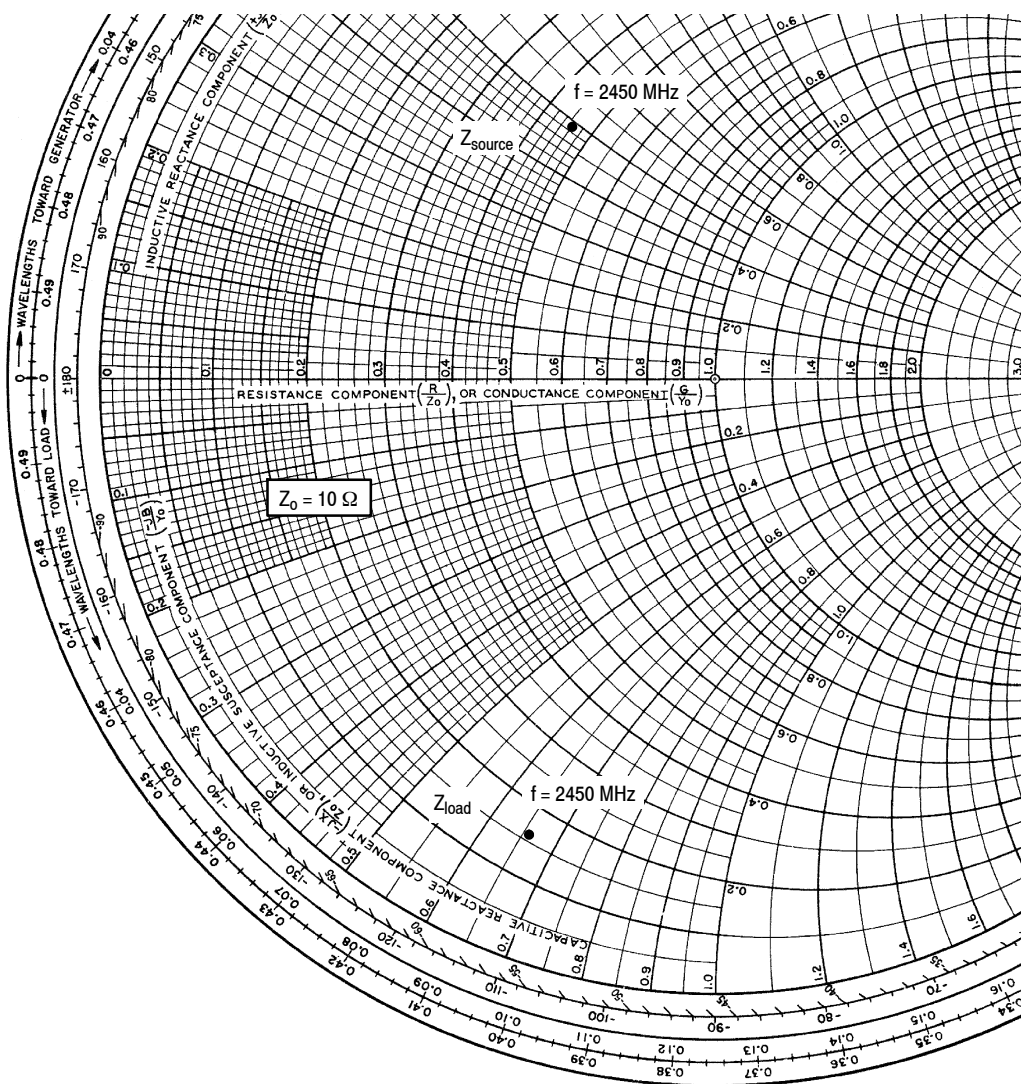


Figure 5. Power Gain and Drain Efficiency versus CW Output Power as a Function of Total I_{DQ}



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1200 \text{ mA}$, $P_{out} = 140 \text{ W CW}$

f MHz	Z_{source} Ω	Z_{load} Ω
2450	$4.55 + j4.9$	$1.64 - j6.57$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

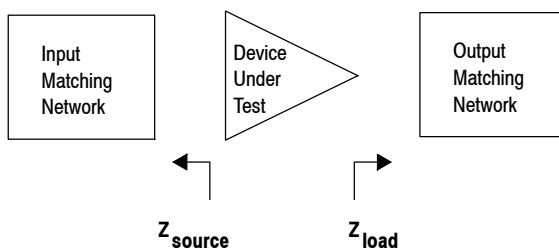
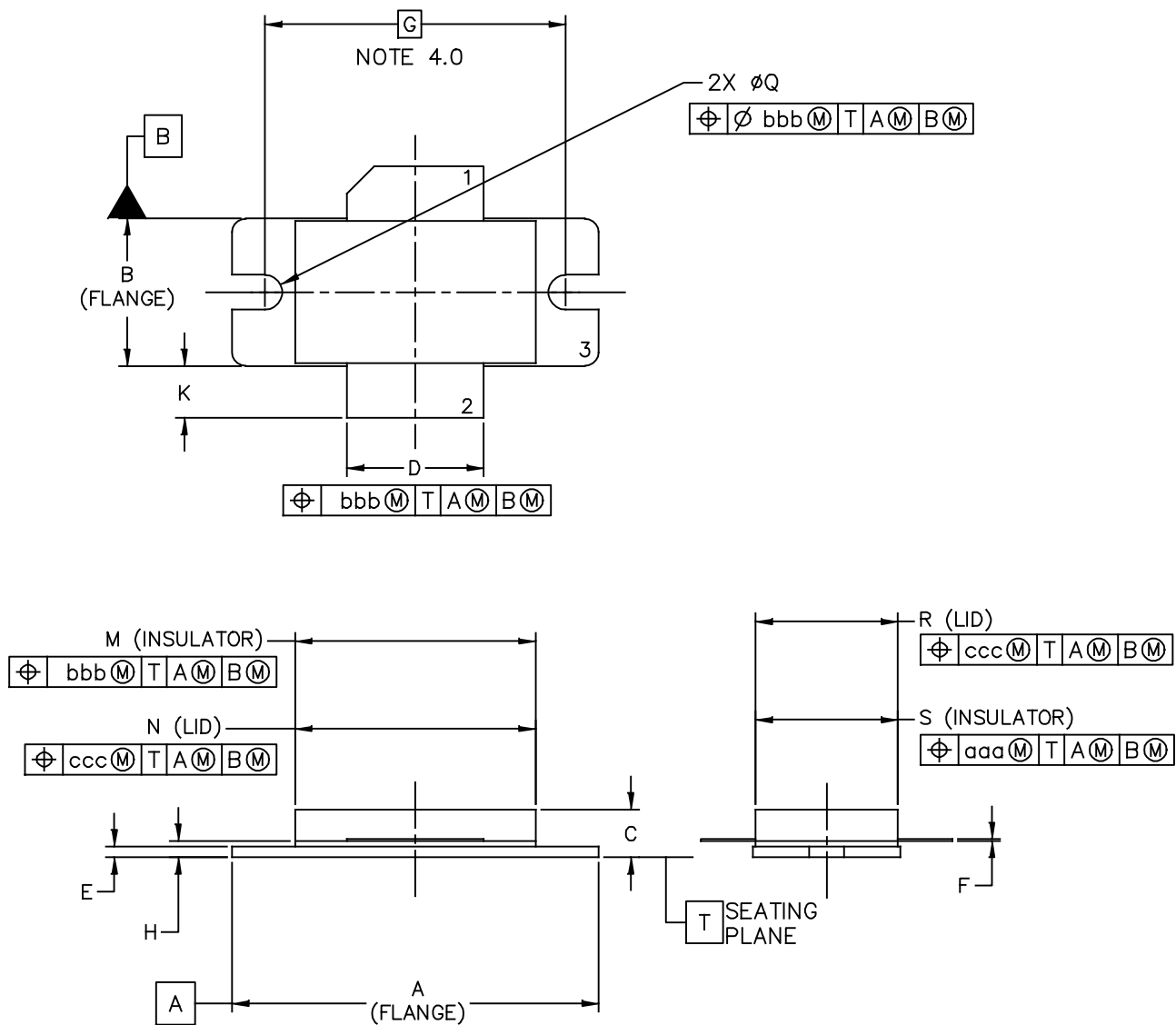


Figure 6. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



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		CASE NUMBER: 465B-04	26 MAY 2011
		STANDARD: NON-JEDEC	

NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
- 2.0 CONTROLLING DIMENSION: INCH.
- 3.0 DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.
- 4.0 RECOMMENDED BOLT CENTER DIMENSION OF 1.16 (29.57) BASED ON M3 SCREW.

INCH			MILLIMETER		INCH			MILLIMETER		
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX	
A	1.335	1.345	33.91	34.16	R	.515	— .525	13.08	— 13.34	
B	.535	.545	13.59	13.84	S	.515	— .525	13.08	— 13.34	
C	.147	.200	3.73	5.08	aaa	— .007	—	— 0.178	—	
D	.495	.505	12.57	12.83	bbb	— .010	—	— 0.254	—	
E	.035	.045	0.89	1.14	ccc	— .015	—	— 0.381	—	
F	.003	.006	0.08	0.15	—	—	—	—	—	
G	1.100 BSC		27.94 BSC		—	—	—	—	—	
H	.057	.067	1.45	1.70	—	—	—	—	—	
K	.175	.205	4.45	5.21	—	—	—	—	—	
M	.872	.888	22.15	22.56	—	—	—	—	—	
N	.871	.889	22.12	22.58	—	—	—	—	—	
Q	ø.118	ø.138	ø3.00	ø3.51	—	—	—	—	—	
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TITLE: NI—880					DOCUMENT NO: 98ARB18493C			REV: F		
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PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following resources to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	May 2014	<ul style="list-style-type: none"> • Initial Release of Data Sheet

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